

SANYO	No.2261A	2SA1562
	PNP Epitaxial Planar Silicon Transistor	
High-h _{FE} , AF Amp Applications		

Applications

- . AF amp, various drivers

Features

- . Adoption of MBIT process
- . High DC current gain
- . Large current capacity
- . Low collector to emitter saturation voltage
- . High V_{EBO}

Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V _{CBO}	-30	V	unit
Collector to Emitter Voltage	V _{CEO}	-25	V	
Emitter to Base Voltage	V _{EBO}	-15	V	
Collector Current	I _C	-1.2	A	
Collector Current(Pulse)	I _{CP}	-2	A	
Collector Dissipation	P _C	1	W	
		15	W	Tc=25°C
Junction Temperature	T _J	150	°C	
Storage Temperature	T _{stg}	-55 to +150	°C	

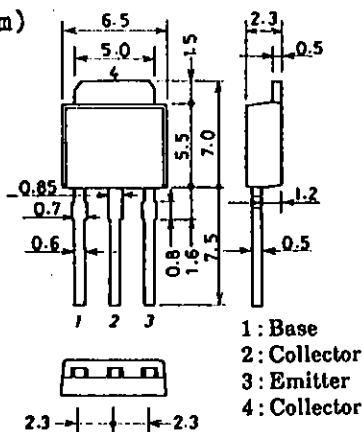
Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I _{CBO} V _{CB} =-20V, I _E =0			-1	μA
Emitter Cutoff Current	I _{EBO} V _{EB} =-10V, I _C =0			-1	μA
DC Current Gain	h _{FE} (1) V _{CE} =-5V, I _C =-100mA	500	800	1200	
	h _{FE} (2) V _{CE} =-5V, I _C =-10mA	350			
Gain-Bandwidth Product	f _T V _{CE} =-10V, I _C =-50mA		130		MHz
Output Capacitance	c _{ob} V _{CB} =-10V, f=1MHz		40		pF
C-E Saturation Voltage	V _{CE(sat)} I _C =-500mA, I _B =-10mA	-0.1	-0.5		V
B-E Saturation Voltage	V _{BE(sat)} I _C =-500mA, I _B =-10mA	-0.78	-1.1		V

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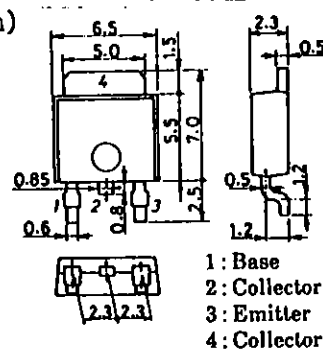
Package Dimensions 2045B

(unit:mm)



Package Dimensions 2044B

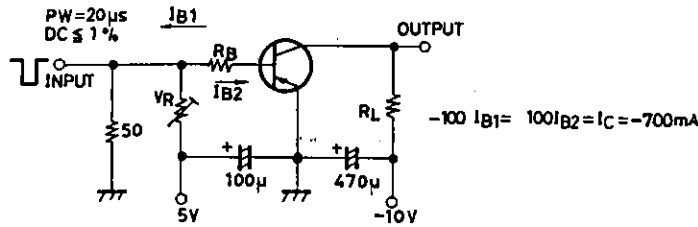
(unit:mm)



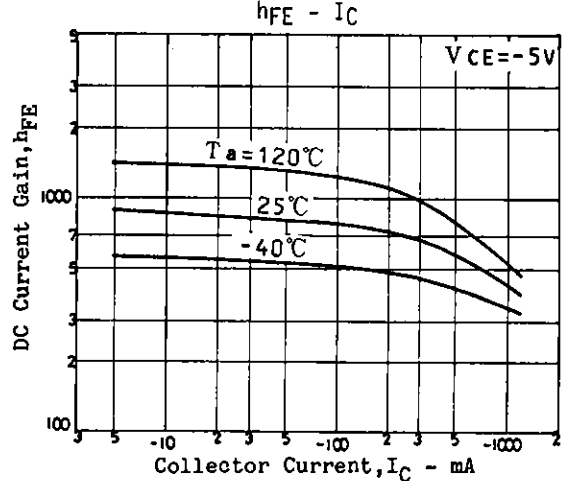
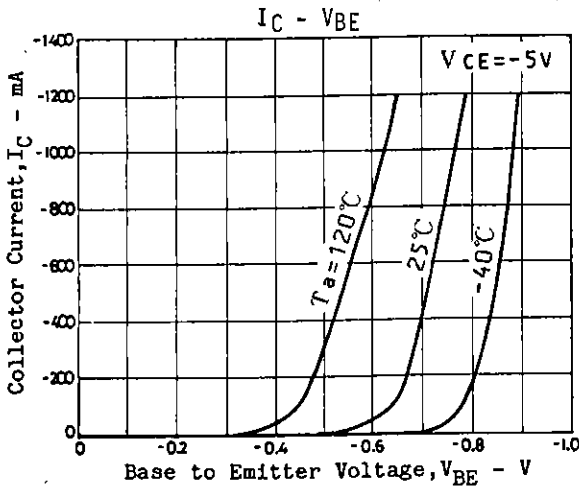
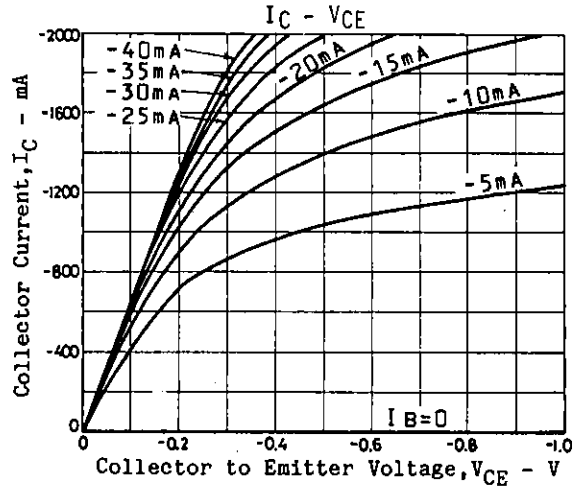
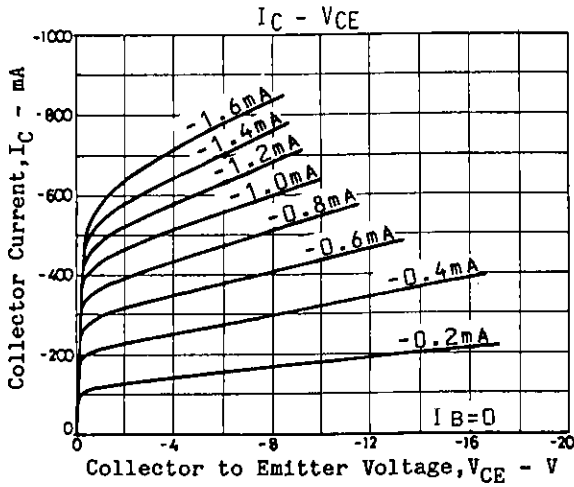
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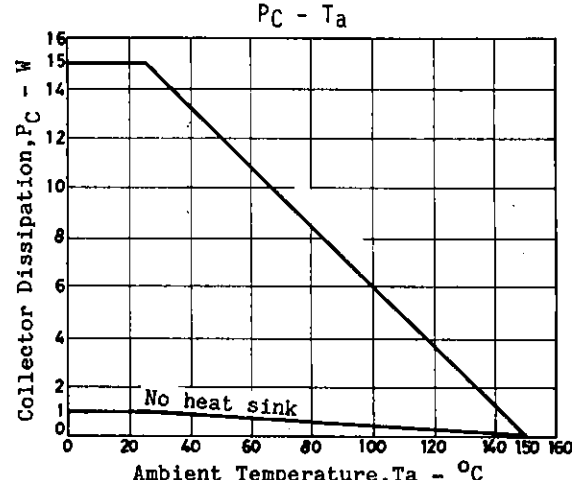
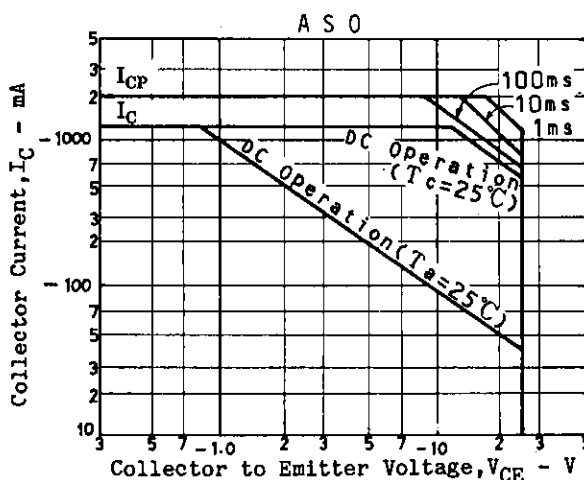
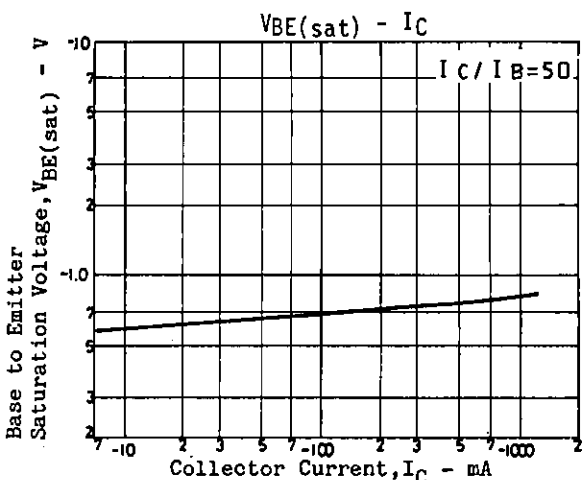
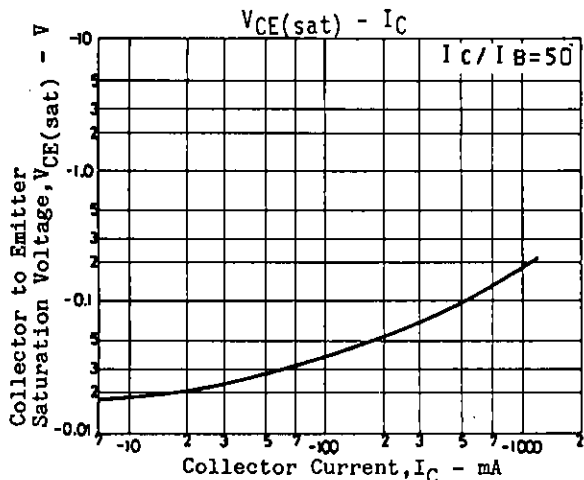
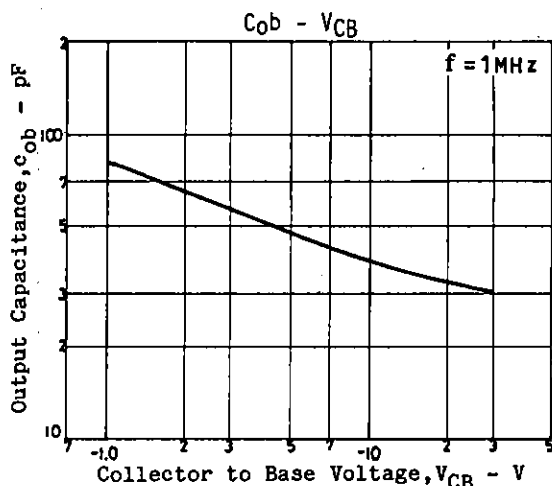
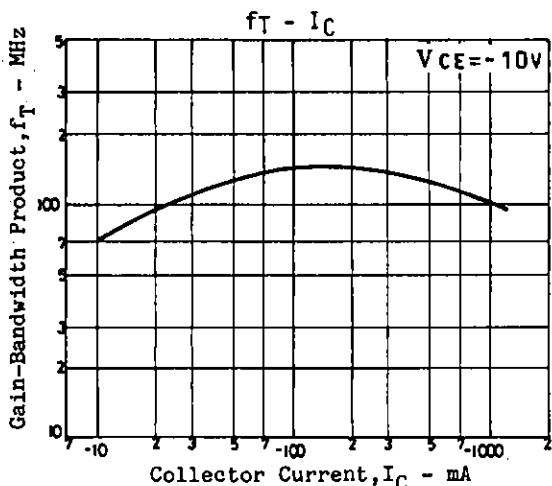
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10\mu A, I_E = 0$	-30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-15			V
Turn-ON Time	t_{on}	See specified Test Circuit.	0.31			μs
Storage Time	t_{stg}	"	0.88			μs
Fall Time	t_f	"	0.23			μs

Switching Time Test Circuit



Unit (Resistance : Ω , Capacitance : F)





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